

Page 3, line 5, after "people" insert --,--;

line 17, delete "one-dot chain", before "line" insert --dashed--; and

line 19, change "therefor" to --therefore--.

Page 6, line 16, after "layer" insert --11--; and

line 18, before "group" insert --a--.

IN THE CLAIMS:

Kindly cancel claims 1-20 and add the following new claims.

21. A method of manufacturing a light-emitting device comprising forming a light-emitting layer comprised of $\text{In}_x\text{Ga}_{1-x}\text{N}$, wherein the light-emitting layer has an indium mole fraction X and emits light of wavelength λ (nm) = $1239.8/E_g$ (eV), over a sapphire substrate; such that the emitted light has an energy level $E_g < 3.4 * (1 - X) + 1.95 * X - 1.0 * X * (1 - X)$.

22. A method according to claim 21, wherein the emitted light has an energy level E_g approximately calculated in accordance with the following: $E_g = 3.4 * (1 - X) + 1.95 * X - 4.26 * X * (1 - X)$.

23. A method according to claim 22, wherein the indium mole fraction X is set from about 0.13 to about 0.18 and the light-emitting layer emits light having a peak wavelength ranging from 460 nm to 480 nm.

24. A method according to claim 22, wherein the indium mole fraction X ranges from about 0.13 to about 0.18 and the light-emitting layer emits blue light.

25. A method according to claim 22, wherein the indium mole fraction X is set from about 0.20 to about 0.23 and the light-emitting layer emits light having a peak wavelength ranging from 510 nm to 530 nm.

26. A method according to claim 22, wherein the indium mole fraction X ranges from about 0.19 to about 0.26, and the light-emitting layer emits green light.

27. A method according to claim 21 further comprising:
disposing a buffer layer comprising AlN on the sapphire substrate;
interposing a first clad layer comprising n-GaN between the buffer layer and the light-emitting layer; and
forming a second clad layer comprising p-GaN doped with magnesium over the light-emitting layer.

28. A method according to claim 27 further comprising:
disposing a transparent electrode comprising gold on the second clad layer; and
disposing an electrode pad on the first clad layer.

29. A method according to claim 27 further comprising:
interposing a layer comprising $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}$ (including $X=0$, $Y=0$, $X=Y=0$), wherein said interposed layer has a wide band gap and is doped with an acceptor, between the light-emitting layer and the second clad layer.

30. A method according to claim 29, wherein the acceptor is a group IIA element.